



IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





BYC10X-600P

Hyperfast power diode

9 May 2014

Product data sheet

1. General description

Hyperfast power diode in a SOD113A (2-lead TO-220-F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $T_h \leq 61$ °C; square-wave pulse; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	10	A
Static characteristics						
V_F	forward voltage	$I_F = 10$ A; $T_j = 150$ °C; Fig. 6	-	1.3	2	V
Dynamic characteristics						
t_{rr}	reverse recovery time	$I_F = 1$ A; $V_R = 30$ V; $di_F/dt = 200$ A/ μ s; $T_j = 25$ °C; Fig. 7	-	12	18	ns

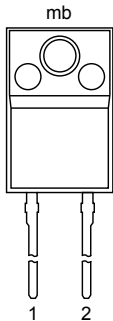



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 <p>TO-220F (SOD113A)</p>	
2	A	anode		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYC10X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220F "full pack"	SOD113A

7. Marking

Table 4. Marking codes

Type number	Marking code
BYC10X-600P	BYC10X-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $T_h \leq 61\text{ }^\circ\text{C}$; square-wave pulse; Fig. 1 ; Fig. 2 ; Fig. 3	-	10	A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25\text{ }\mu\text{s}$; $T_h \leq 61\text{ }^\circ\text{C}$; square-wave pulse	-	20	A

Symbol	Parameter	Conditions	Min	Max	Unit
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(initial)} = 25 °C; sine-wave pulse; Fig. 4	-	150	A
		t _p = 8.3 ms; T _{j(initial)} = 25 °C; sine-wave pulse; Fig. 4	-	165	A
T _{stg}	storage temperature		-65	175	°C
T _j	junction temperature		-	175	°C

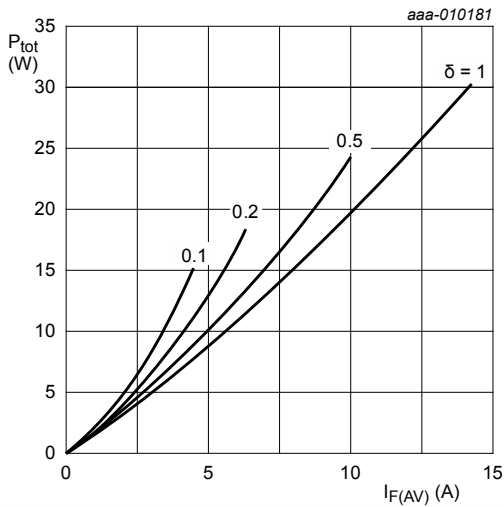


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_O = 1.572 \text{ V}; R_S = 0.040 \text{ } \Omega$$

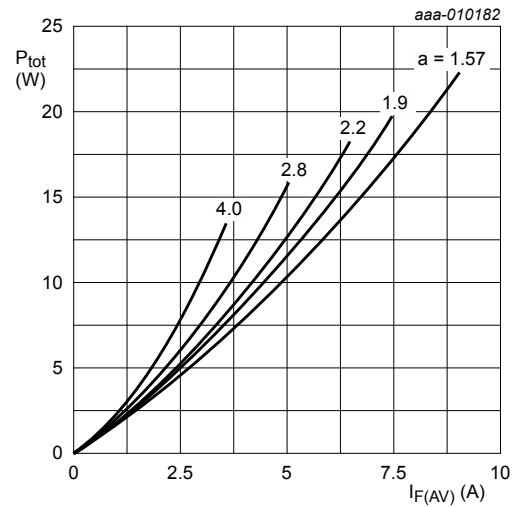


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$

$$V_O = 1.572 \text{ V}; R_S = 0.040 \text{ } \Omega$$

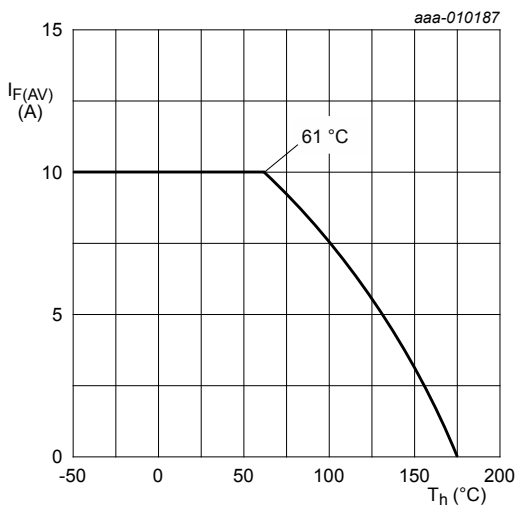


Fig. 3. Forward current as a function of heatsink temperature; maximum values

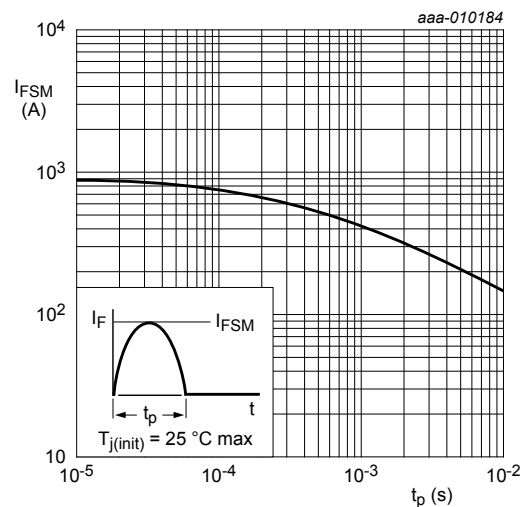


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig. 5	-	-	4.8	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W

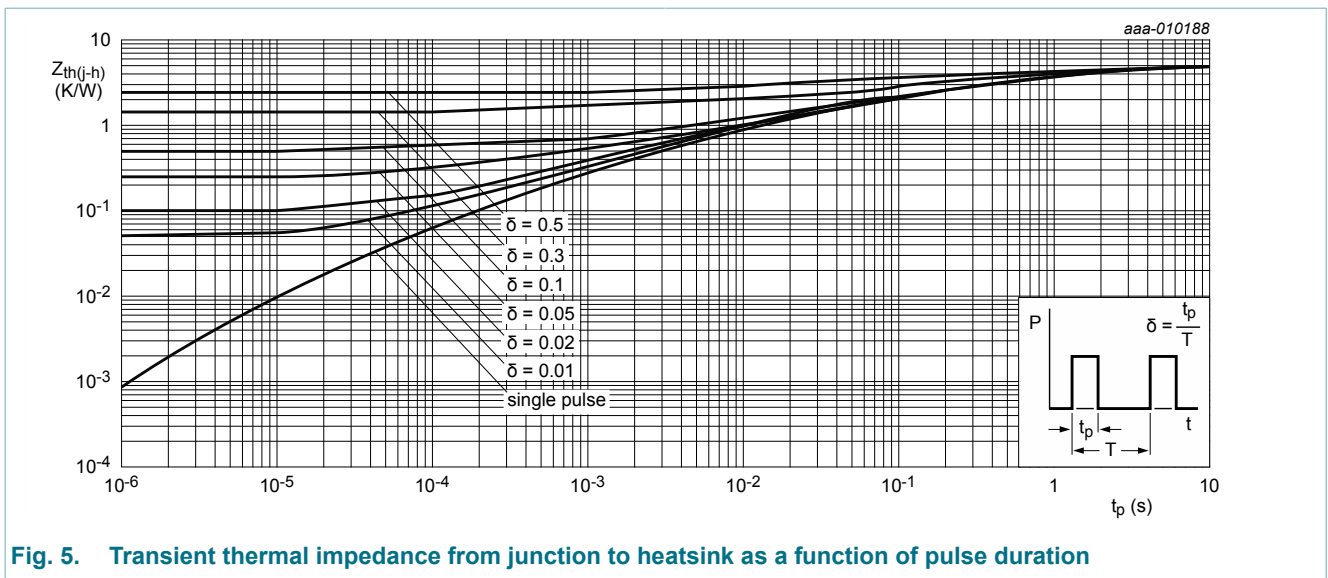


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C_{isol}	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward voltage	$I_F = 10\text{ A}$; $T_j = 25\text{ °C}$; Fig. 6	-	2.5	3.2	V

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$I_F = 10\text{ A}; T_j = 150\text{ }^\circ\text{C}; \text{Fig. 6}$	-	1.3	2	V
I_R	reverse current	$V_R = 600\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	-	10	μA
		$V_R = 600\text{ V}; T_j = 150\text{ }^\circ\text{C}$	-	-	0.8	mA
Dynamic characteristics						
Q_r	recovered charge	$I_F = 10\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 7}$	-	26	-	nC
		$I_F = 10\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 125\text{ }^\circ\text{C}; \text{Fig. 7}$	-	83	-	nC
t_{rr}	reverse recovery time	$I_F = 1\text{ A}; V_R = 30\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 7}$	-	12	18	ns
		$I_F = 10\text{ A}; V_R = 400\text{ V}; dI_F/dt = 500\text{ A}/\mu\text{s}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 7}$	-	19	-	ns
		$I_F = 10\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 7}$	-	26	-	ns
		$I_F = 10\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 125\text{ }^\circ\text{C}; \text{Fig. 7}$	-	34	-	ns
I_{RM}	peak reverse recovery current	$I_F = 10\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 7}$	-	2	-	A
		$I_F = 10\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 125\text{ }^\circ\text{C}; \text{Fig. 7}$	-	4.8	-	A

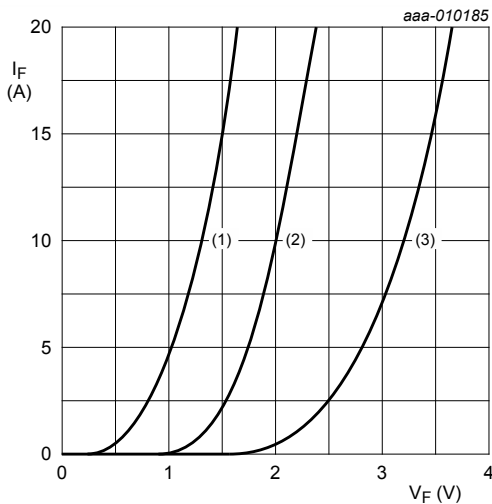


Fig. 6. Forward current as a function of forward voltage

- (1) $T_j = 150\text{ }^\circ\text{C};$ typical values;
 - (2) $T_j = 150\text{ }^\circ\text{C};$ maximum values;
 - (3) $T_j = 25\text{ }^\circ\text{C};$ maximum values;
- $V_O = 1.572\text{ V}; R_S = 0.040\ \Omega$

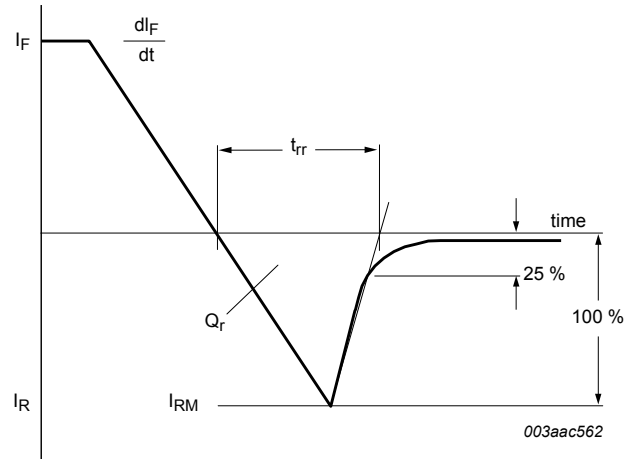
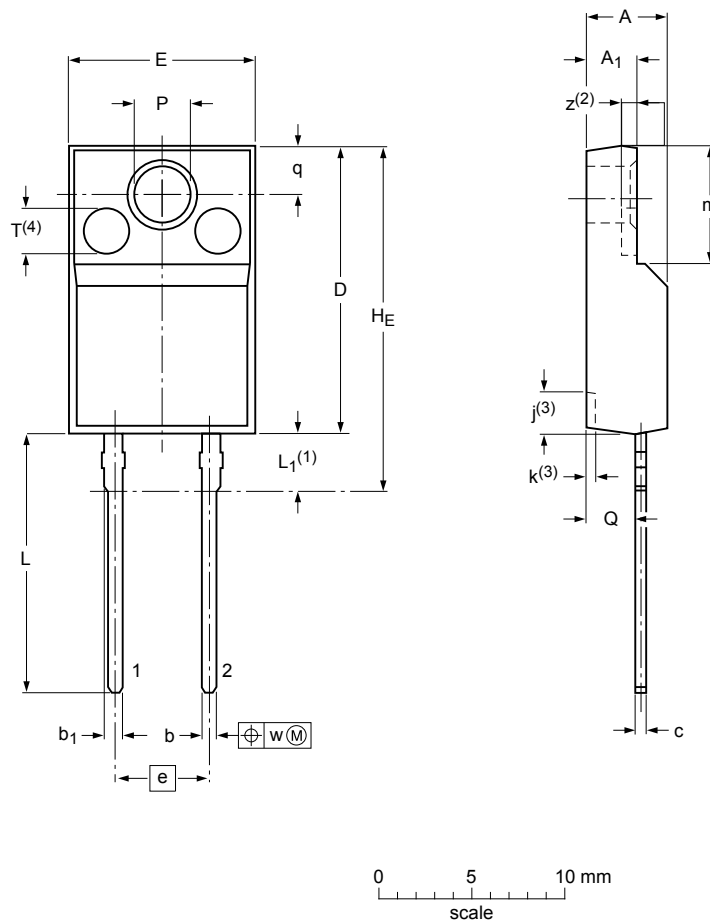


Fig. 7. Reverse recovery definitions; ramp recovery

12. Package outline

Plastic single-ended package; isolated heasink mounted;
1 mounting hole; 2-lead TO-220F 'full pack'

SOD113A



Dimensions (mm are the original dimensions)

Unit	A	A ₁	b	b ₁	c	D	E	e	H _E max	j ⁽³⁾	k ⁽³⁾	L	L ₁ ⁽¹⁾	m	P	Q	q	T ⁽⁴⁾	W	z ⁽²⁾	
mm	max	4.6	3.1	0.9	1.1	0.7	15.8	10.3		2.7	0.8	14.4	3.3	6.5	3.2	2.8		2.6	2.55	0.4	0.8
	nom							5.08	19.0												
	min	4.0	2.5	0.7	0.9	0.4	15.2	9.7		1.7	0.4	13.5	2.8	6.3	3.0	2.3					

Note

1. Terminals are uncontrolled within zone L1.
2. z is depth of T.
3. Dot lines area designs may vary.
4. Eject pin mark is for reference only.

sod113a_po

Outline version	References			European projection	Issue date
	IEC	JEDEC	JEITA		
SOD113A	2 LEADS TO220F				14-01-14 14-04-10

Fig. 8. Package outline TO-220F (SOD113A)

13. Legal information

13.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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